

STFW3N150, STH3N150-2, STP3N150, STW3N150

N-channel 1500 V, 2.5 A, 6 Ω typ., PowerMESH™ Power MOSFETs
in TO-3PF, H²PAK-2, TO-220 and TO247 packages

Datasheet - production data

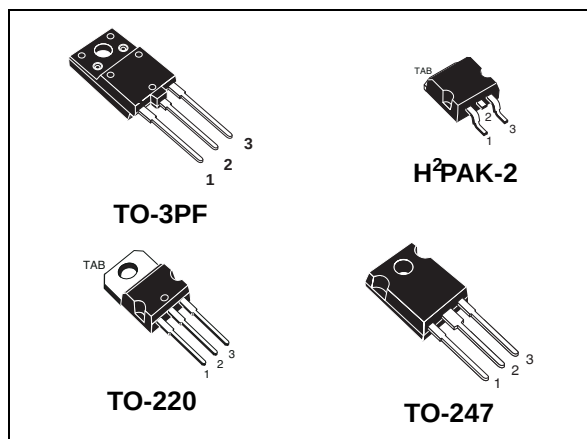
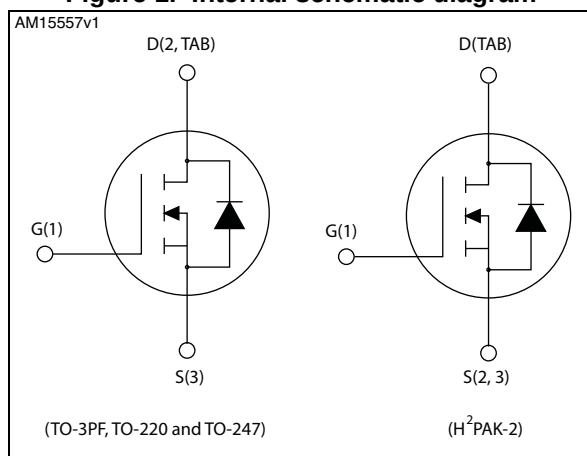


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STFW3N150	1500 V	9 Ω	2.5 A	63 W
STH3N150-2				140 W
STP3N150				
STW3N150				

- 100% avalanche tested
- Intrinsic capacitances and Q_g minimized
- High speed switching
- Fully isolated TO-3PF plastic package, creepage distance path is 5.4 mm (typ.)

Applications

- Switching applications

Description

These Power MOSFETs are designed using the company's consolidated strip layout-based MESH OVERLAY™ process. The result is a product that matches or improves on the performance of comparable standard parts from other manufacturers.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STFW3N150	3N150	TO-3PF	Tube
STH3N150-2		H ² PAK-2	Tape and reel
STP3N150		TO-220	Tube
STW3N150		TO-247	

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 **Electrical characteristics (curves)** 6

3 **Test circuits** 9

4 **Package mechanical data** 10

5 **Packaging mechanical data** 20

6 **Revision history** 22



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-3PF	H ² PAK-2, TO-220, TO-247	
V _{DS}	Drain-source voltage	1500		V
V _{GS}	Gate-source voltage	± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	2.5 ⁽¹⁾	2.5	A
I _D	Drain current (continuous) at T _C = 100 °C	1.6 ⁽¹⁾	1.6	A
I _{DM} ⁽¹⁾	Drain current (pulsed)	10 ⁽¹⁾	10	A
P _{TOT}	Total dissipation at T _C = 25 °C	63	140	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	3500		V
	Derating factor	0.5	1.12	W/°C
T _{stg}	Storage temperature	-50 to 150		°C
T _j	Max. operating junction temperature	150		°C

1. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	TO-3PF	H ² PAK-2	TO-220	TO-247	Unit
R _{thj-case}	Thermal resistance junction-case max	2	0.89			°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	50		62.5	50	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max		35 ⁽¹⁾			°C/W

1. When mounted on 1 inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	2.5	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	450	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{\text{GS}} = 0$	1500			V
I_{DSS}	Zero gate voltage drain current ($V_{\text{GS}} = 0$)	$V_{\text{DS}} = 1500\text{ V}$			10	μA
		$V_{\text{DS}} = 1500\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}$			500	μA
I_{GSS}	Gate-body leakage current ($V_{\text{DS}} = 0$)	$V_{\text{GS}} = \pm 30\text{ V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_D = 1.3\text{ A}$		6	9	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{\text{fs}}^{(1)}$	Forward transconductance	$V_{\text{DS}} = 30\text{ V}$, $I_D = 1.3\text{ A}$	-	2.6	-	S
C_{iss}	Input capacitance	$V_{\text{DS}} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0$	-	939	-	pF
			-		-	pF
			-		-	pF
C_{oss}	Output capacitance		-	102	-	pF
C_{rss}	Reverse transfer capacitance		-	13.2	-	pF
$C_{\text{oss eq.}}^{(2)}$	Equivalent output capacitance	$V_{\text{DS}} = 0$ to 1200 V , $V_{\text{GS}} = 0$	-	100	-	pF
R_g	Gate input resistance	$f = 1\text{ MHz}$, gate DC Bias = 0, test signal level = 20 mV, $I_D = 0$	-	4	-	Ω
Q_g	Total gate charge	$V_{\text{DD}} = 1200\text{ V}$, $I_D = 2.5\text{ A}$,	-	29.3	-	nC
Q_{gs}	Gate-source charge	$V_{\text{GS}} = 10\text{ V}$	-	4.6	-	nC
Q_{gd}	Gate-drain charge	(Figure 19)	-	17	-	nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 750 \text{ V}$, $I_D = 1.25 \text{ A}$, $R_G = 4.7 \text{ } \Omega$, $V_{GS} = 10 \text{ V}$ (Figure 18)	-	24	-	ns
t_r	Rise time		-	47	-	ns
$t_{d(off)}$	Turn-off-delay time		-	45	-	ns
t_f	Fall time		-	61	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		10	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5 \text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (Figure 20)	-	410		ns
Q_{rr}	Reverse recovery charge		-	2.4		μC
I_{RRM}	Reverse recovery current		-	11.7		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$, $T_j = 150 \text{ } ^\circ\text{C}$ (Figure 20)	-	540		ns
Q_{rr}	Reverse recovery charge		-	3.3		μC
I_{RRM}	Reverse recovery current		-	12.3		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-3PF

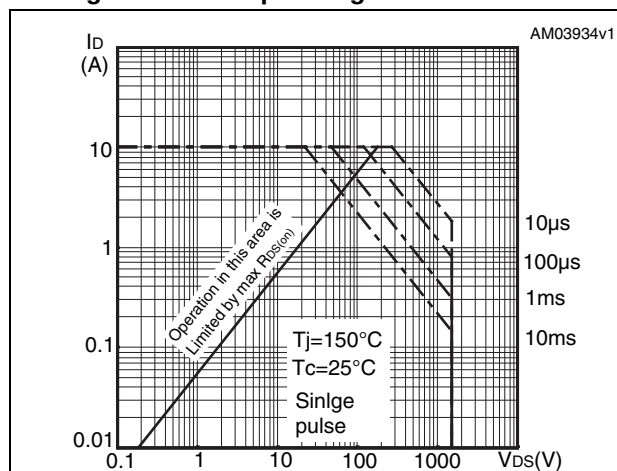


Figure 3. Thermal impedance for TO-3PF

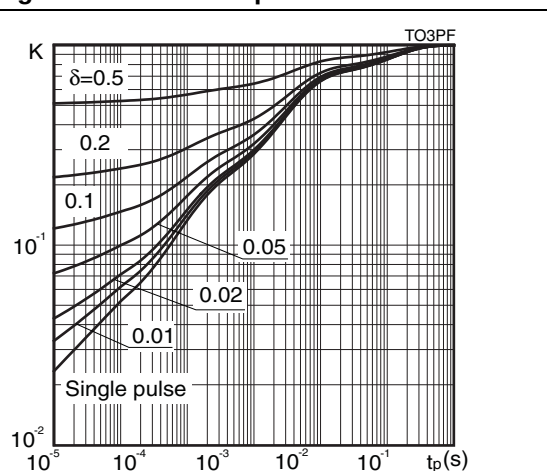
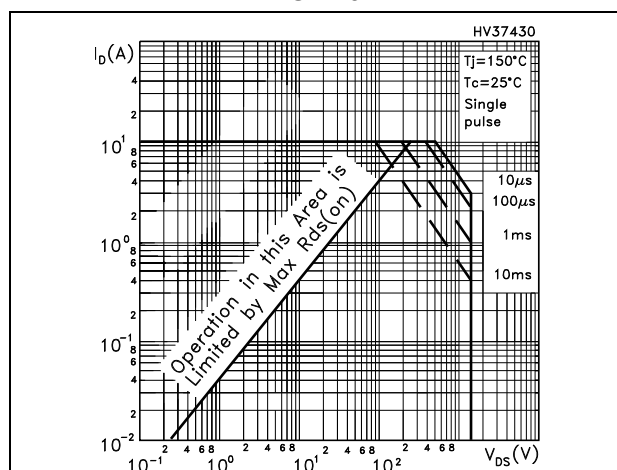
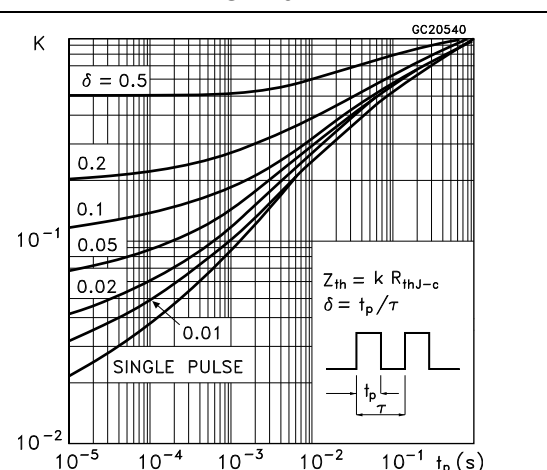
Figure 4. Safe operating area for H²PAK-2 and TO-220Figure 5. Thermal impedance for H²PAK-2 and TO-220

Figure 6. Safe operating area for TO-247

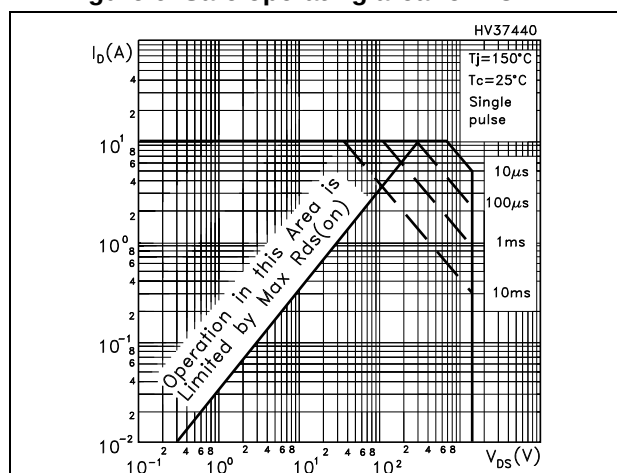


Figure 7. Thermal impedance for TO-247

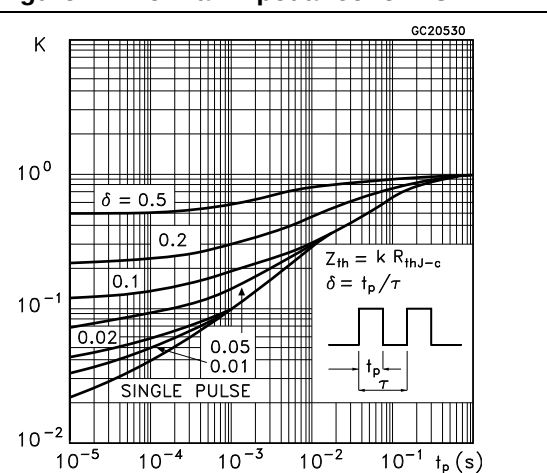


Figure 8. Output characteristics

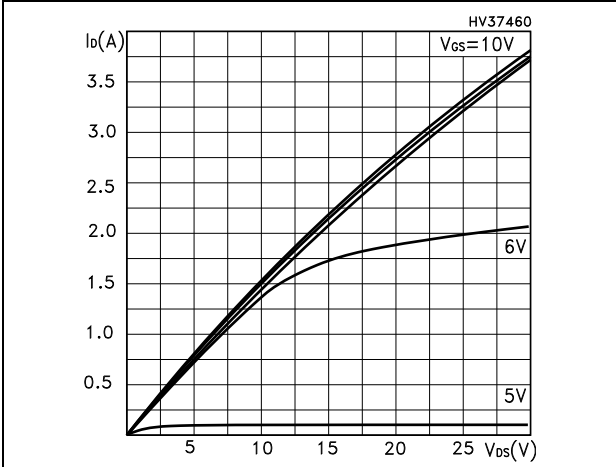


Figure 9. Transfer characteristics

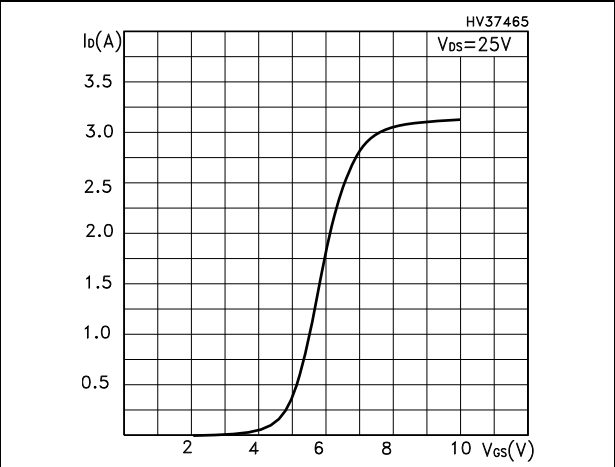


Figure 10. Normalized BV_{DSS} vs. temperature

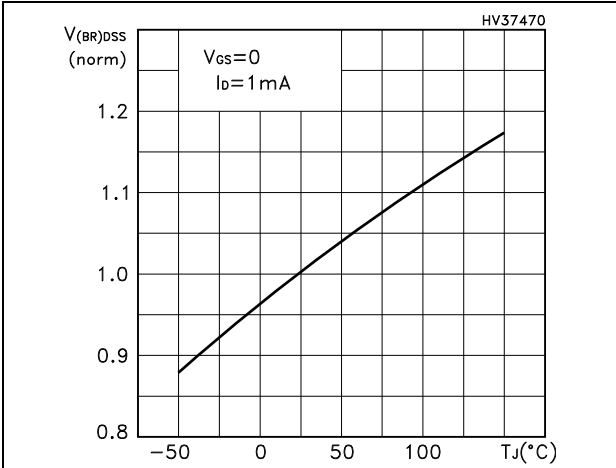


Figure 11. Static drain-source on-resistance

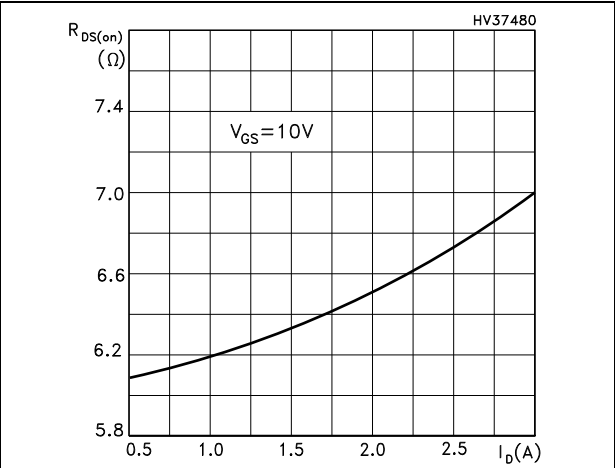


Figure 12. Gate charge vs. gate-source voltage

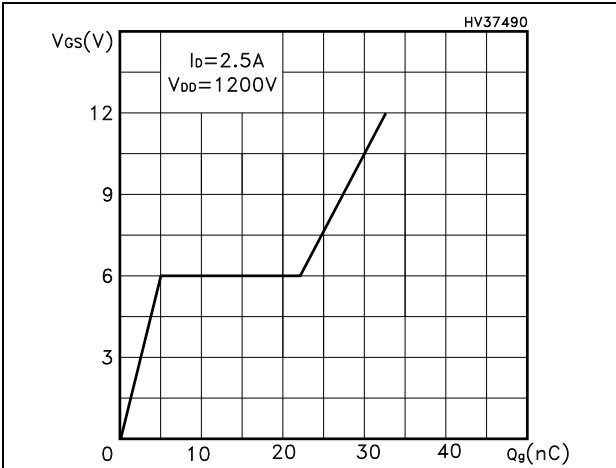


Figure 13. Capacitance variations

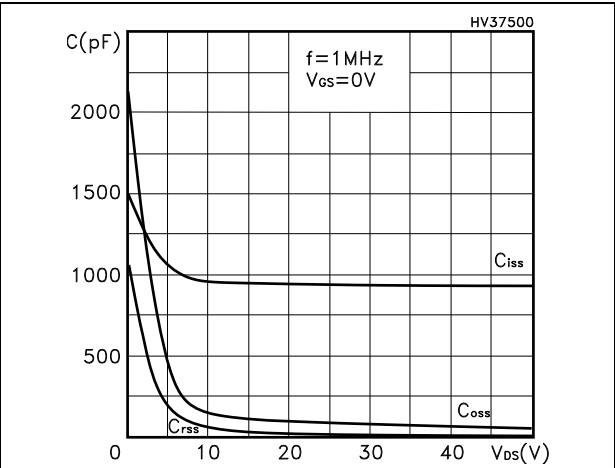


Figure 14. Normalized gate threshold voltage vs. temperature

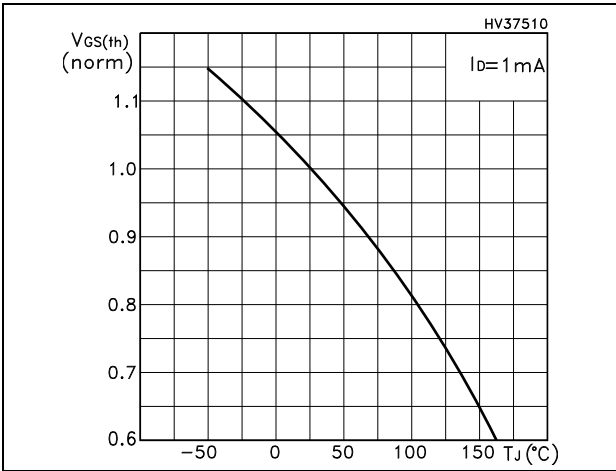


Figure 15. Normalized on resistance vs. temperature

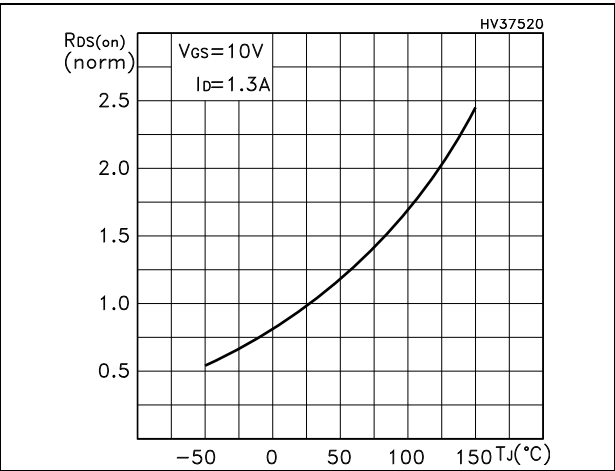


Figure 16. Source-drain diode forward characteristics

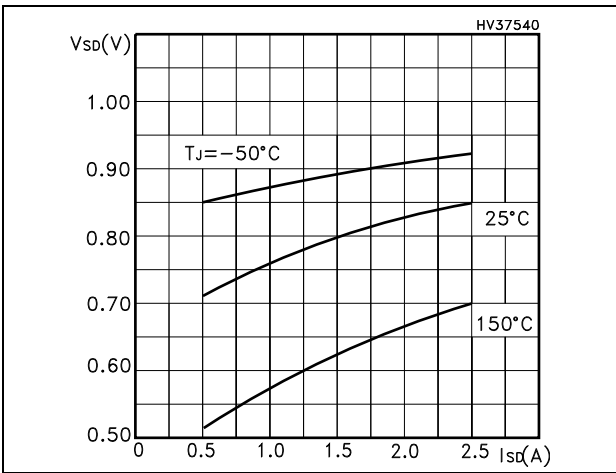
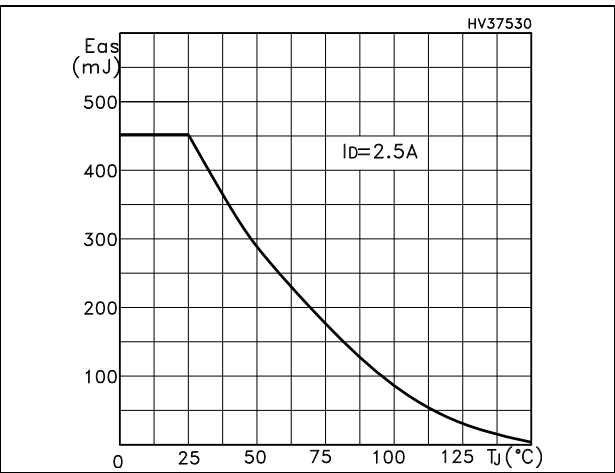


Figure 17. Maximum avalanche energy vs T_J



3 Test circuits

Figure 18. Switching times test circuit for resistive load

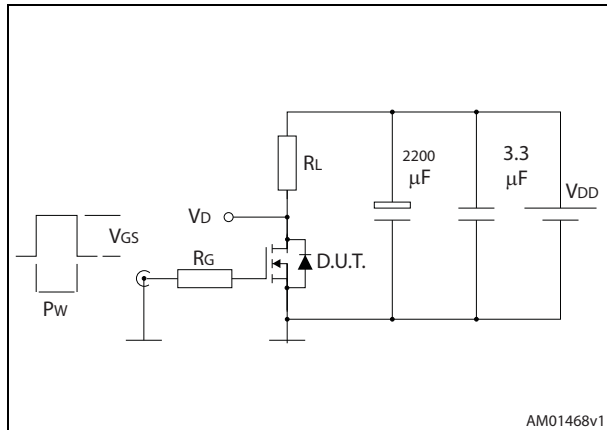


Figure 19. Gate charge test circuit

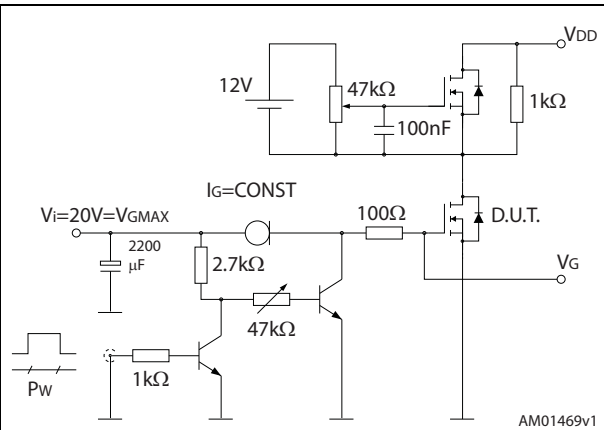


Figure 20. Test circuit for inductive load switching and diode recovery times

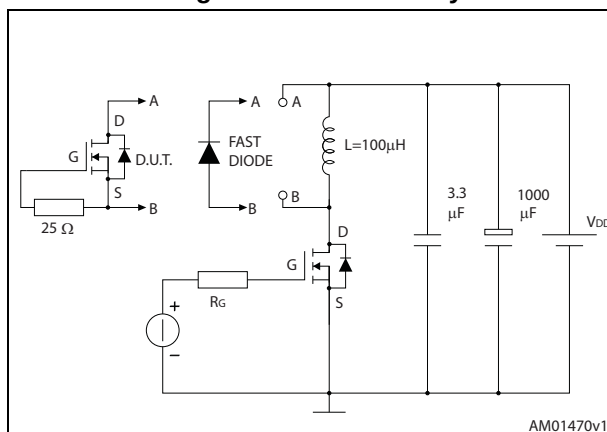


Figure 21. Unclamped inductive load test circuit

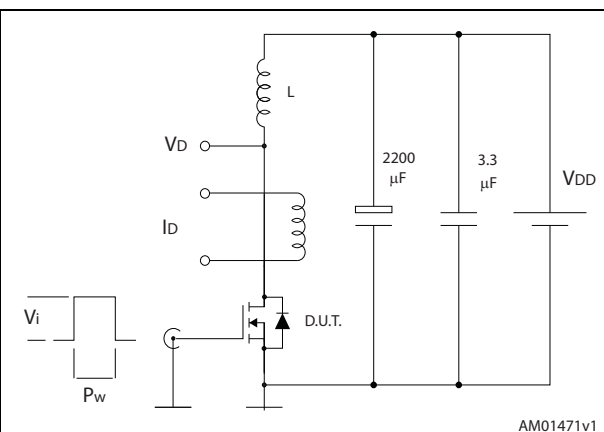


Figure 22. Unclamped inductive waveform

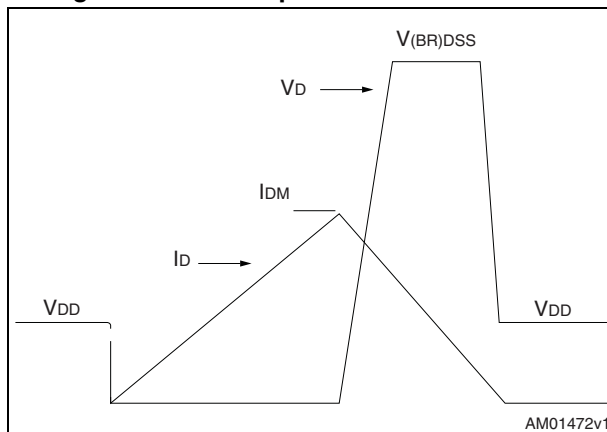
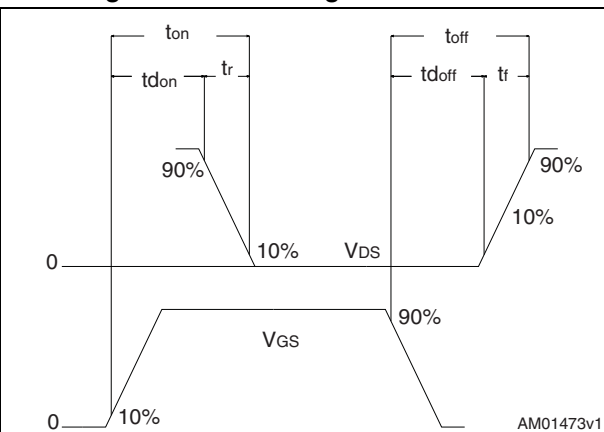


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 24. TO-3PF drawing

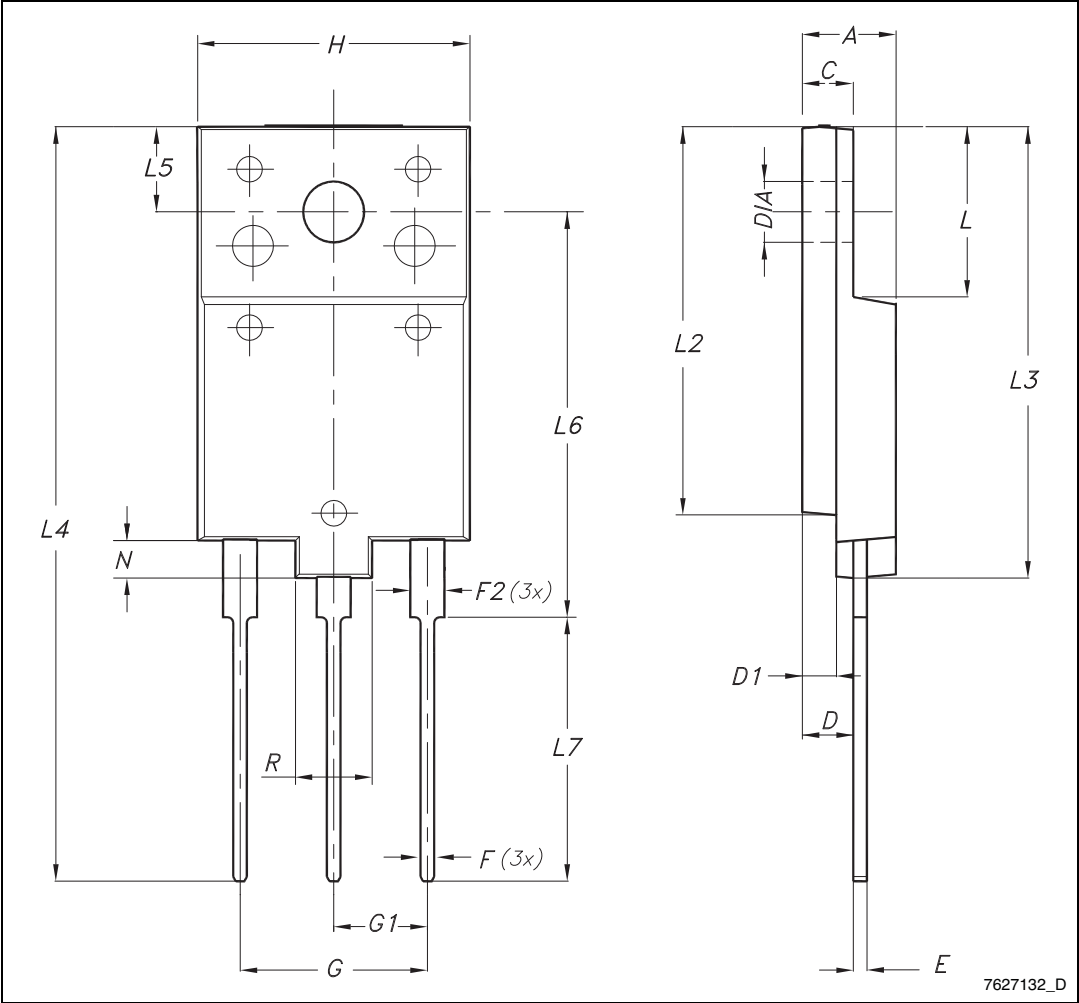


Table 9. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

Figure 25. H²PAK-2 drawing

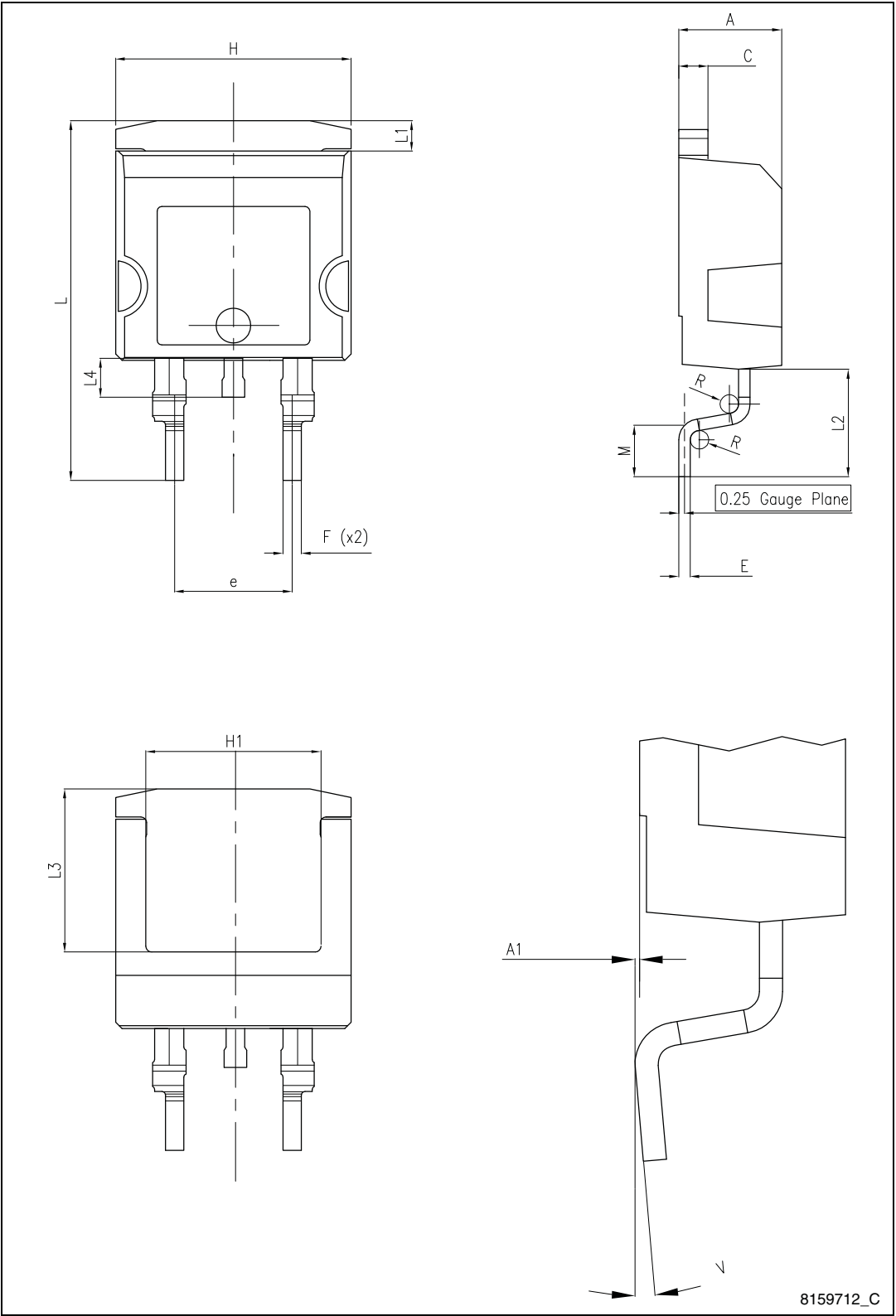


Table 10. H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

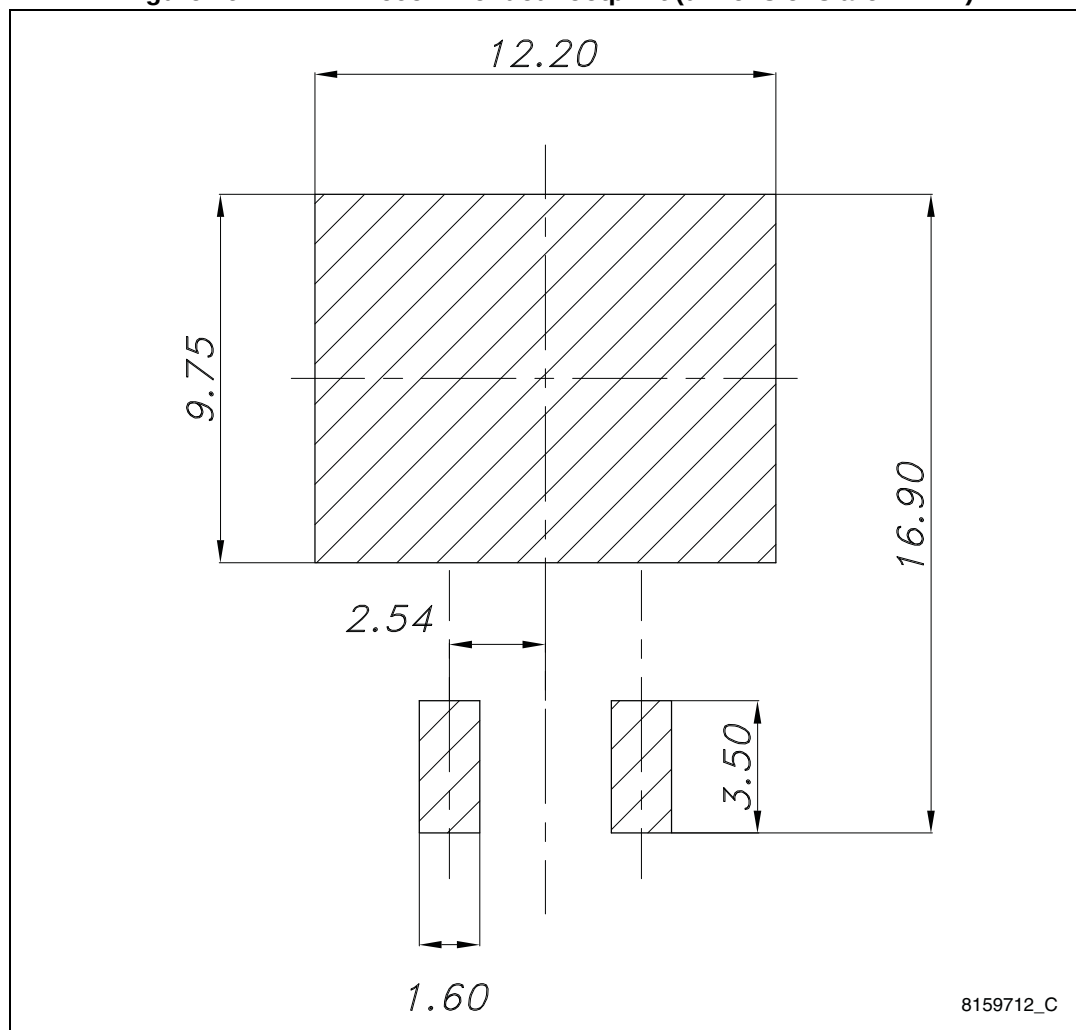
Figure 26. H²PAK-2 recommended footprint (dimensions are in mm)

Figure 27. TO-220 type A drawing

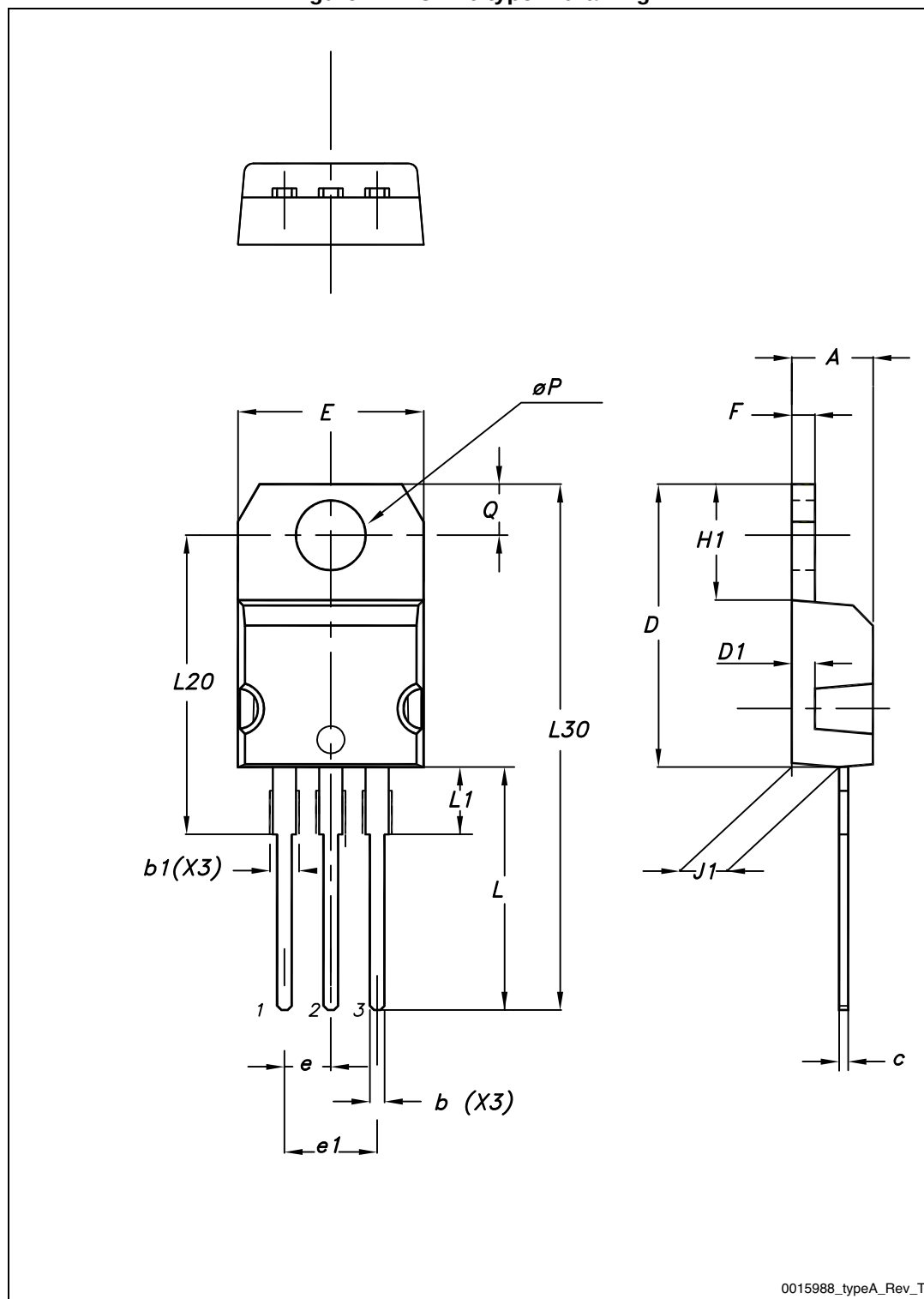


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 28. TO-247 drawing

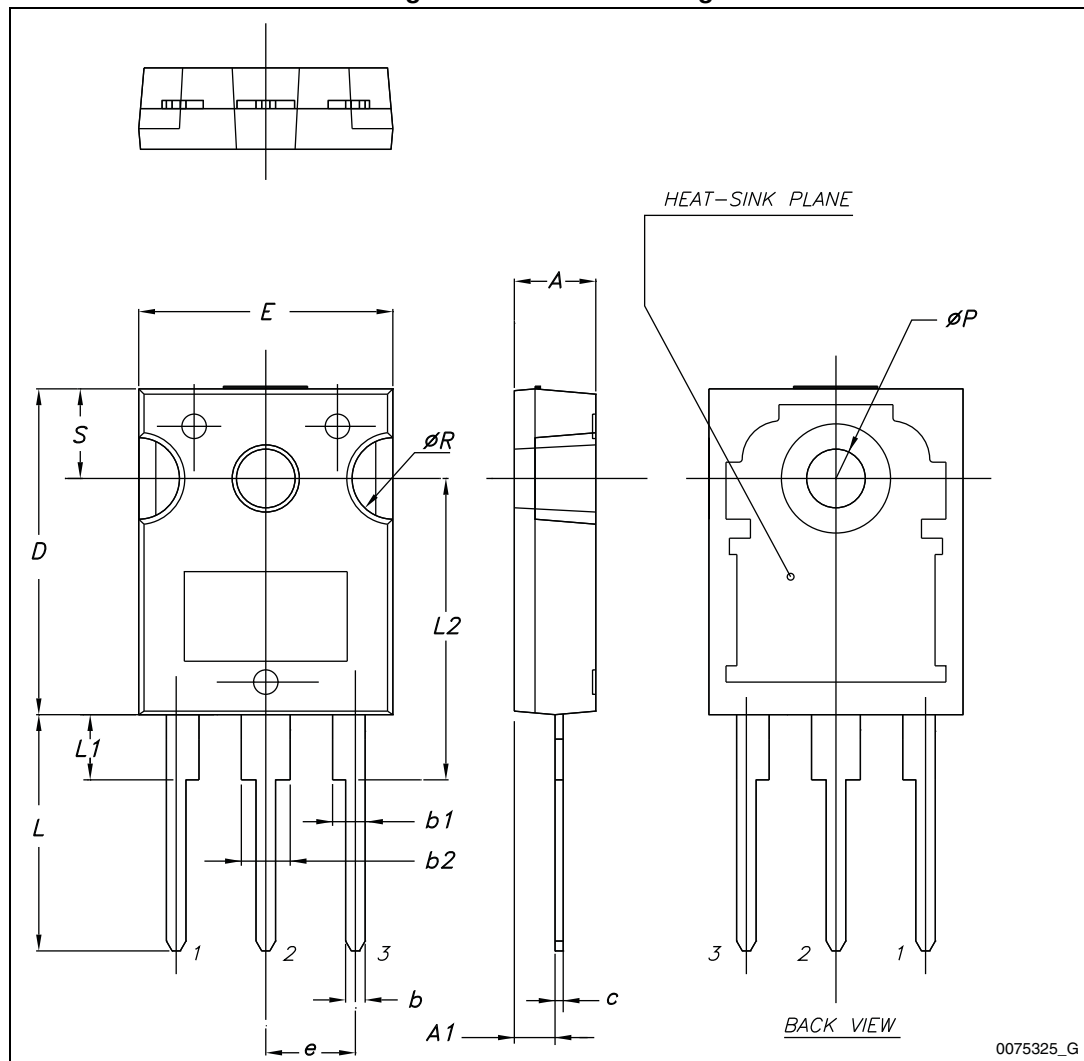


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Packaging mechanical data

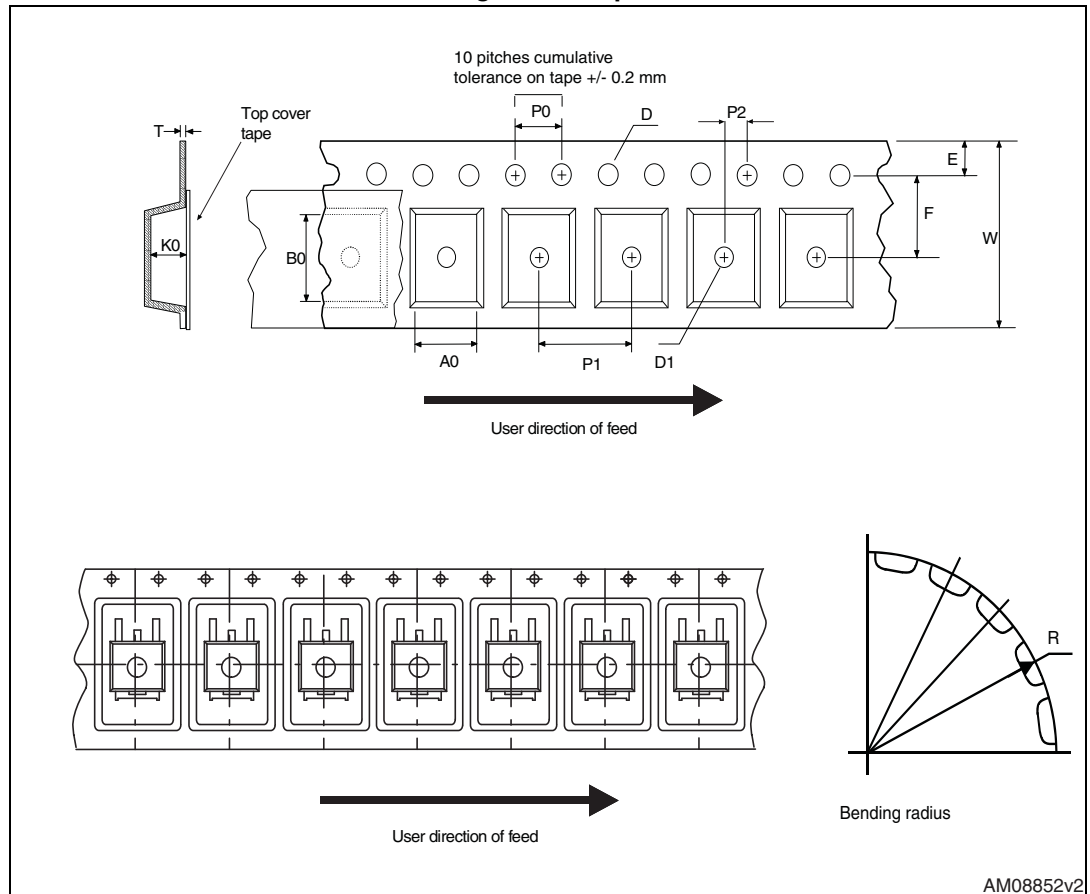
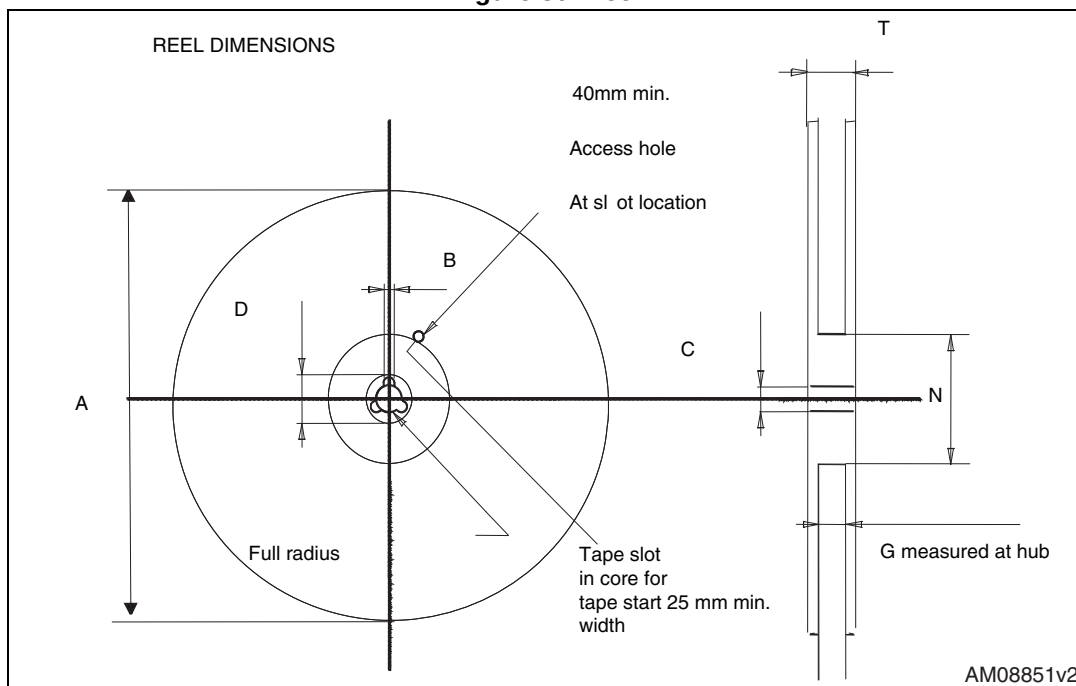
Figure 29. Tape

Figure 30. Reel

Table 13. H²PAK-2 tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

6 Revision history

Table 14. Document revision history

Date	Revision	Changes
12-Jan-2007	1	First release
17-Apr-2007	2	Added new value on Table 6 .
14-May-2007	3	The document has been reformatted
29-Aug-2007	4	$R_{DS(on)}$ value changed, updated Figure 15
09-Apr-2008	5	Added new package: TO-3PF
13-Feb-2009	6	Added P_{TOT} value for TO-3PF (Table 2: Absolute maximum ratings)
01-Dec-2009	7	– Document status promoted from preliminary data to datasheet – Removed TO-220FH package and mechanical data
10-Dec-2009	8	Corrected V_{ISO} value in Table 2: Absolute maximum ratings
29-Jun-2010	9	Corrected unit in Table 3 .
08-Feb-2013	10	– Minor text changes – Modified: Table 3 – Changed: Figure 1 – Added: H²PAK-2 package
18-Feb-2014	11	– Modified: Figure 1 – Updated: Figure 18, 19, 20 and 21 – Updated: Figure 27 and Table 11 – Updated: Section 4: Package mechanical data – Minor text changes

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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